

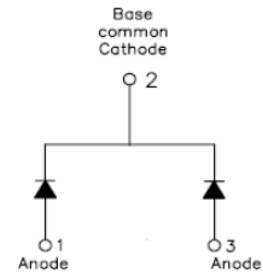
SK10100FC SCHOTTKY RECTIFIER

Applications:

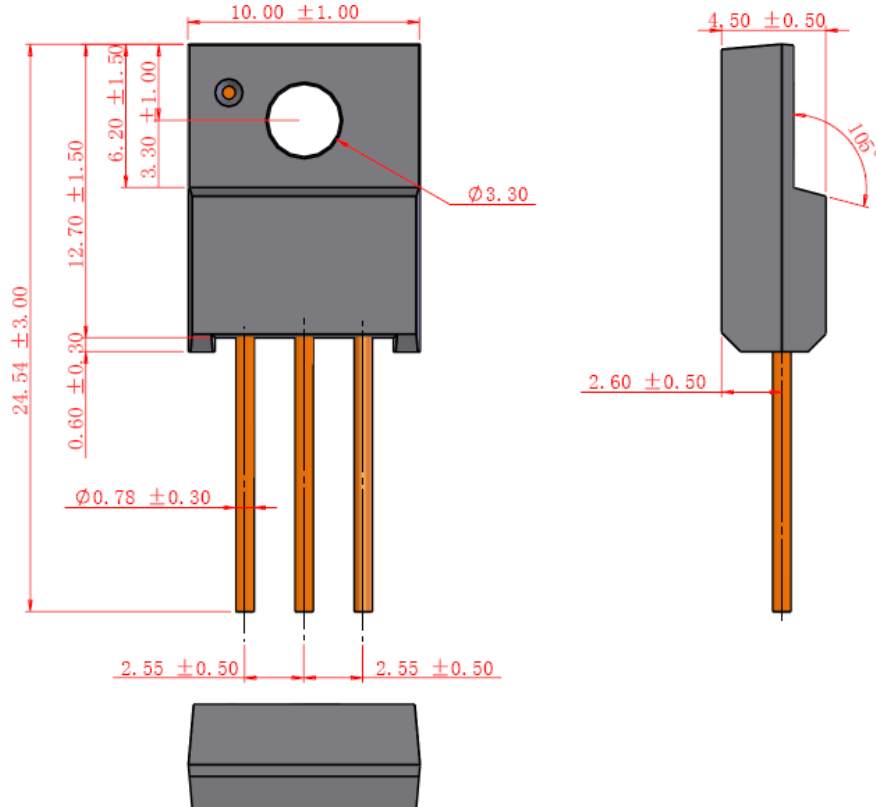
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Dimensions (In mm):



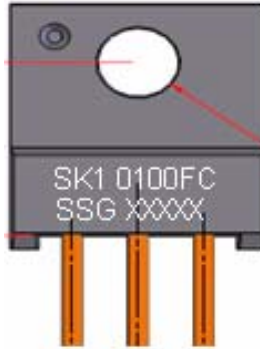
ITO-220AB



Technical Data
Data Sheet N0963, Rev. -

Green Products

Marking Diagram:



Where XXXXX is YYWWL

SK = Device Type
10 = Forward Current (10A)
100 = Reverse Voltage (100V)
FC = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SK10100FC	ITO-220AB (Pb-Free)	50 pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=100^{\circ}C$, rectangular wave form	10	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	120	A



Electrical Characteristics:

*

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 5A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.85	V
	V_{F2}	@ 5 A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.75	V
Max. Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.00	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	15	mA
Max. Junction Capacitance (per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{\text{SIG}} = 1\text{MHz}$	300	pF
Typical Series Inductance (per leg)	L_S	Measured lead to lead 5 mm from package body	8.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case (per leg)	$R_{\theta\text{JC}}$	DC operation	2.0	$^\circ\text{C/W}$
Maximum Thermal Resistance, Case to Heat Sink	$R_{\theta\text{CS}}$	Mounting surface, smooth and greased (only for TO-220)	0.50	$^\circ\text{C/W}$
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

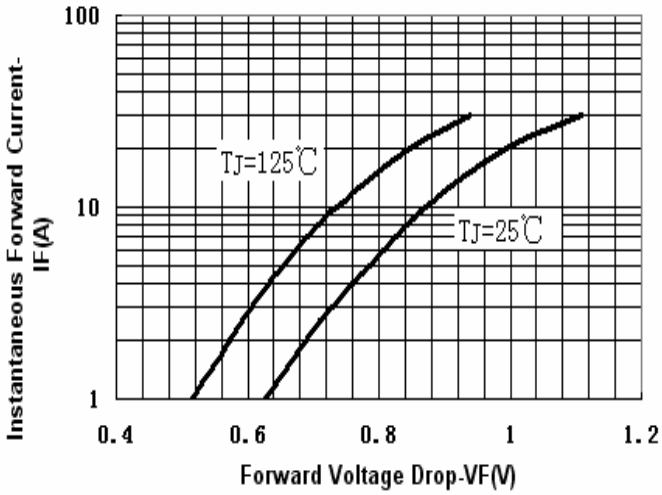


Fig.1-Typical Forward Voltage Drop Characteristics

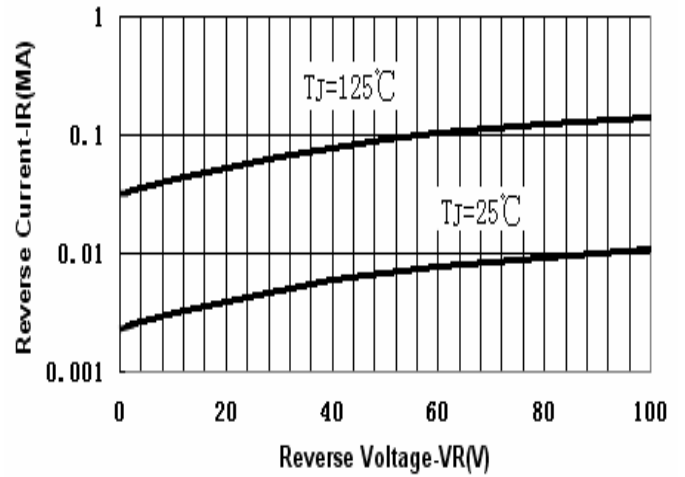


Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

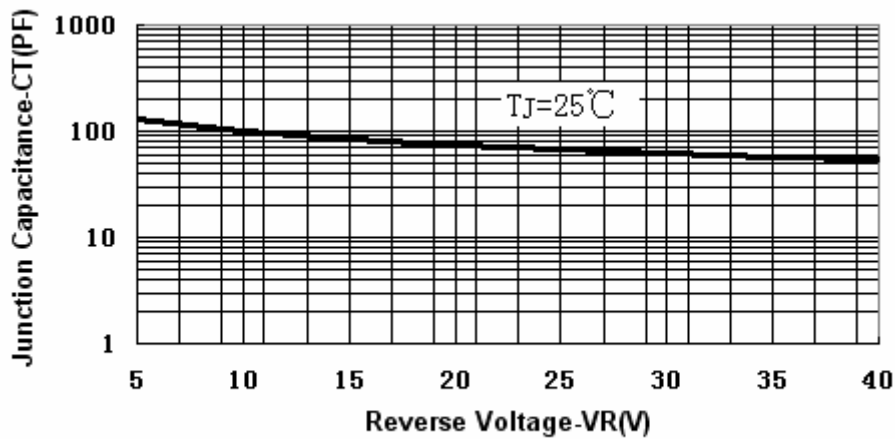


Fig.3-Typical Junction Capacitance Vs.Reverse Voltage



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